

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D $T_A = +25^\circ C$
30V	38m Ω @ $V_{GS} = -10V$	5.8A
	64m Ω @ $V_{GS} = -4.5V$	4.5A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

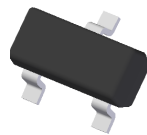
- Load Switch
- DC-DC Converters
- Power Management Functions

Features and Benefits

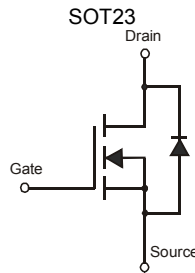
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

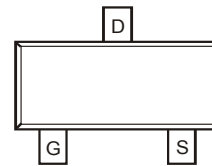
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



Top View



Equivalent Circuit



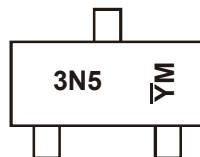
Top View

Ordering Information (Note 4)

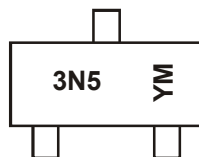
Part Number	Case	Packaging
DMN3051L-7	SOT23	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



Chengdu A/T Site



Shanghai A/T Site

3N5 = Product Type Marking Code
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 Y̅M = Date Code Marking for CAT (Chengdu Assembly/ Test site)
 Y or Y̅ = Year (ex: A = 2013)
 M = Month (ex: 9 = September)

Date Code Key

Year	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	U	V	W	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	4.5 3.5	A
	t < 5s	T _A = +25°C T _A = +70°C	I _D	5.8 4.9	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	20	A
Maximum Body Diode Forward Current (Note 6)			I _S	2	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.7	W
	T _A = +70°C		0.44	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R _{θJA}	182	°C/W
	t < 5s		109	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.4	W
	T _A = +70°C		0.85	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	R _{θJA}	94	°C/W
	t < 5s		56	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	25	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	800	nA	V _{DS} = 28V, V _{GS} = 0V
Gate-Body Leakage	I _{GSS}	—	—	±80 ±800	nA	V _{GS} = ±12V, V _{DS} = 0V V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	1.3	1.9	2.2	V	V _{DS} = V _{GS} , I _D = 250 µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	33	38	mΩ	V _{GS} = 10V, I _D = 5.8A V _{GS} = 4.5V, I _D = 5.0A
		—	54	64		
Forward Transconductance	Y _{fs}	—	5	—	S	V _{DS} = 5V, I _D = 3.1A
Source-Drain Diode Forward Voltage	V _{SD}	—	0.78	1.16	V	V _{GS} = 0V, I _S = 2.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	424	—	pF	V _{DS} = 5V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	115	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	81	—	pF	
Gate Resistance	R _g	—	1.51	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	9.0	—	nC	V _{GS} = 10V, V _{DS} = 15V, I _D = 5.8A
Gate-Source Charge	Q _{gs}	—	1.3	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.3	—	nC	
Turn-On Delay Time	t _{D(on)}	—	3.4	—	ns	V _{DD} = 15V, V _{GS} = 10V, R _L = 2.6Ω, R _G = 3Ω
Turn-On Rise Time	t _r	—	6.2	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	13.9	—	ns	
Turn-Off Fall Time	t _f	—	2.8	—	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

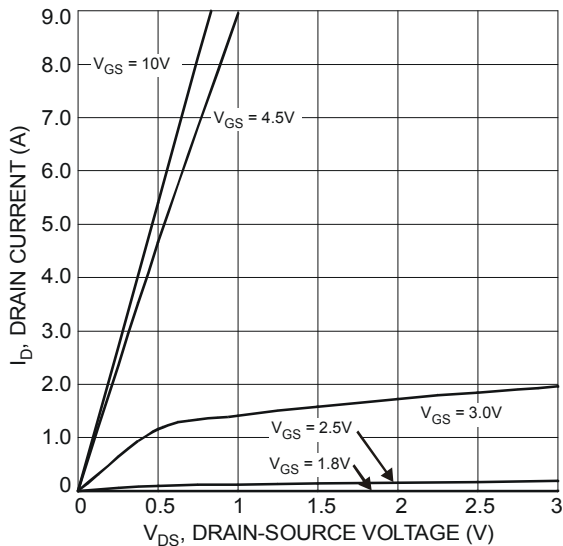


Fig. 1 Typical Output Characteristics

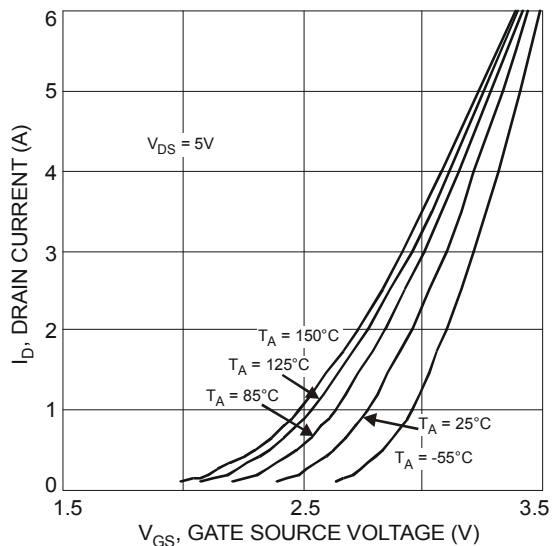


Fig. 2 Typical Transfer Characteristics

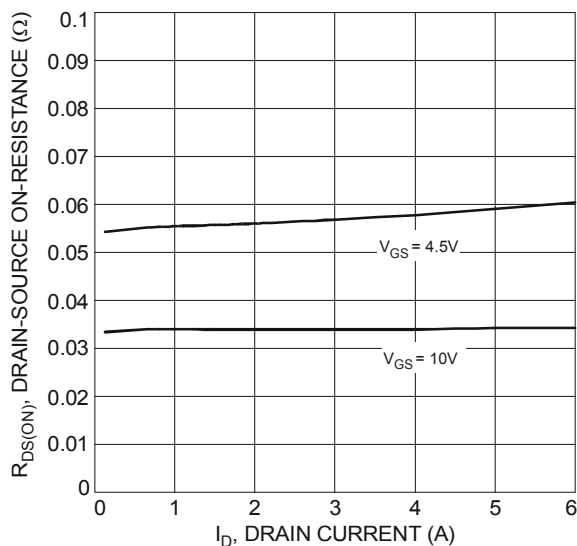


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

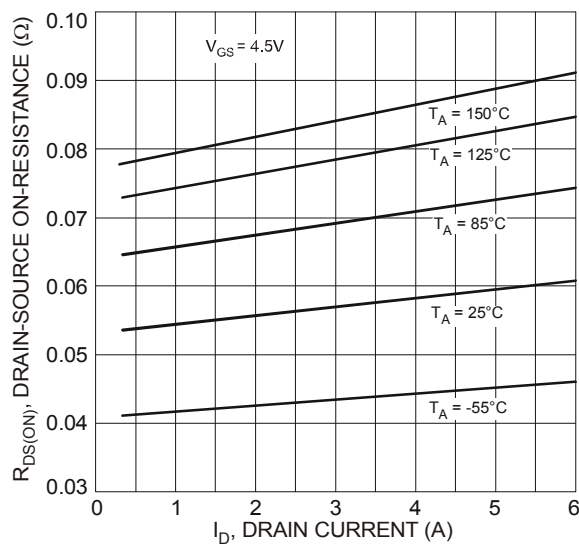


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

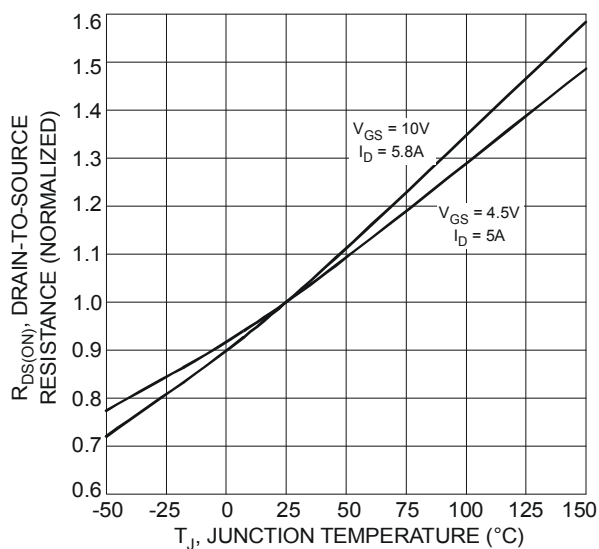


Fig. 5 On-Resistance Variation with Temperature

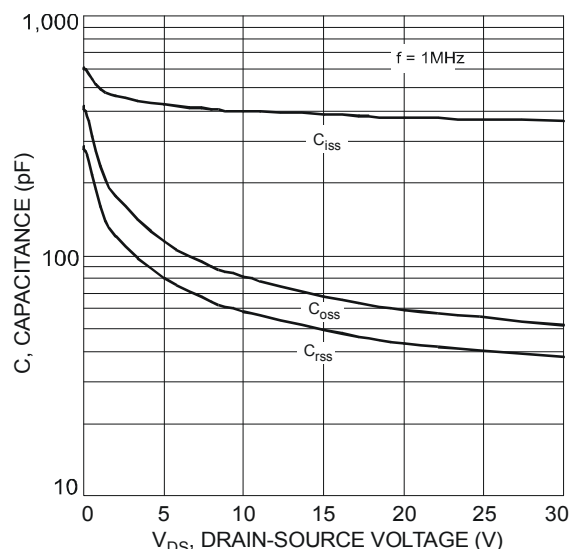


Fig. 6 Typical Capacitance

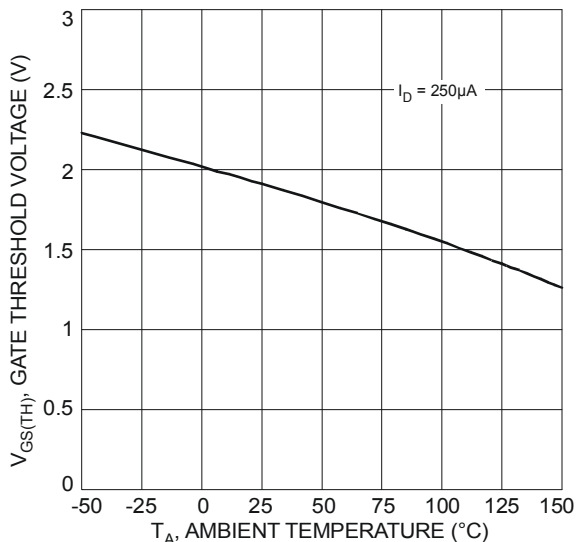


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

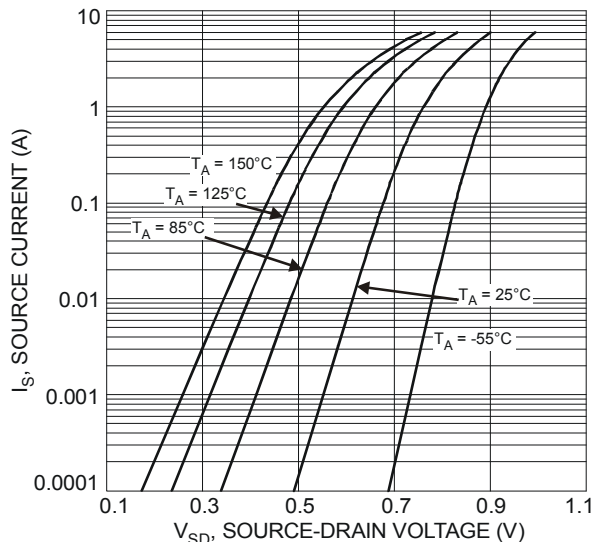


Fig. 8 Diode Forward Voltage vs. Current

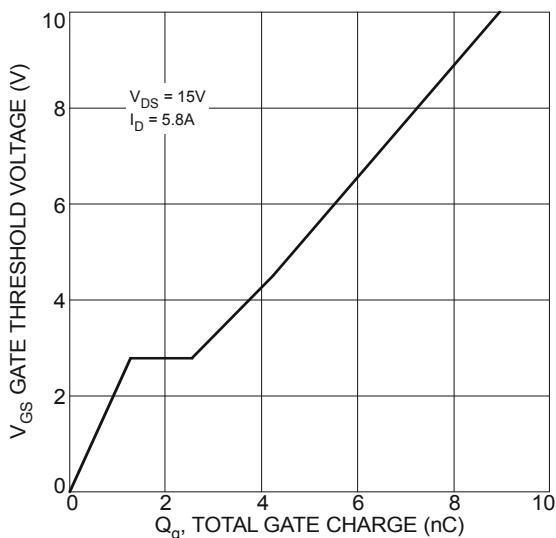


Fig. 9 Gate Charge

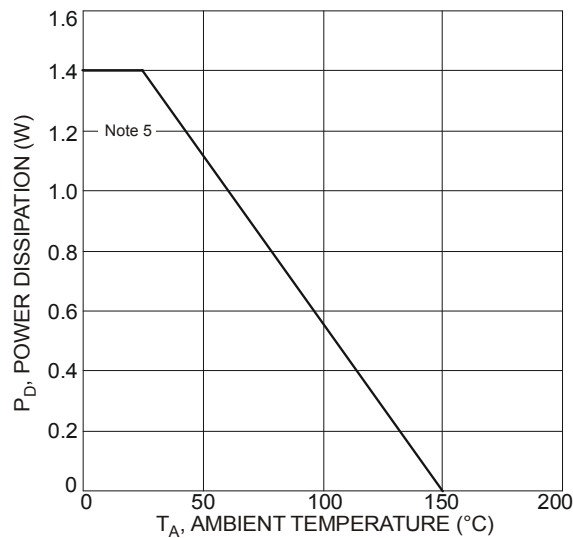


Fig. 10 Power Derating

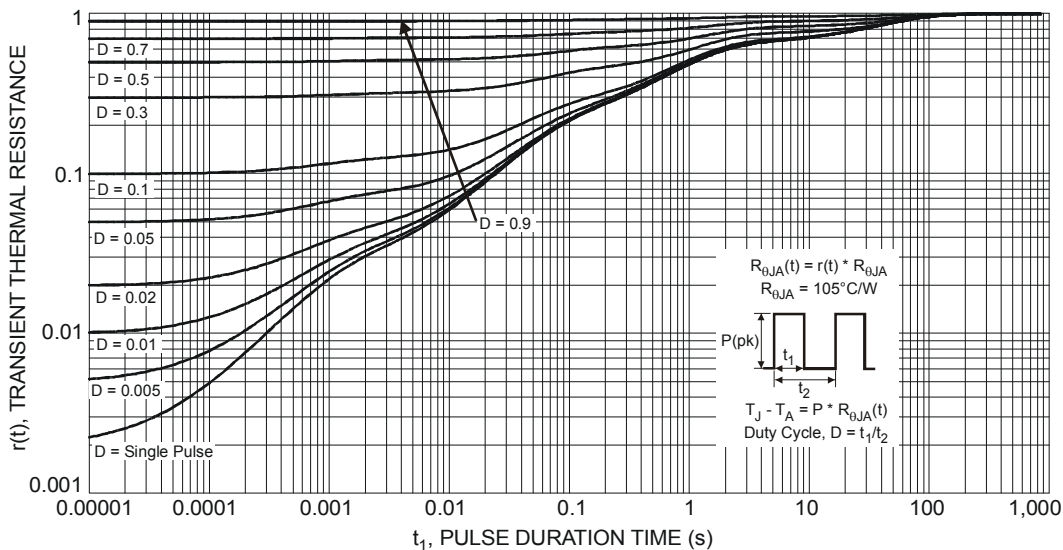
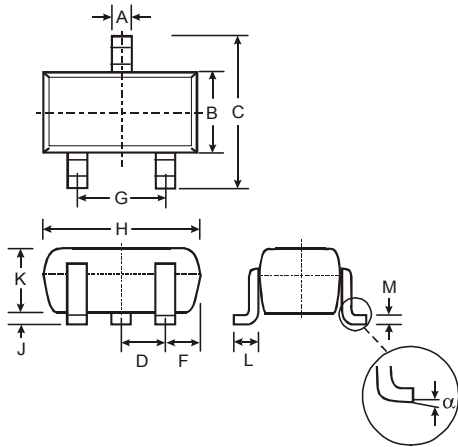


Fig. 11 Transient Thermal Response

Package Outline Dimensions

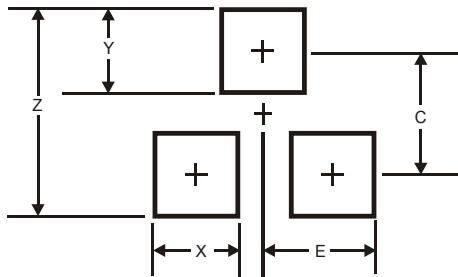
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
F	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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